

**Appl. No.** : **09/584,656**  
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### **AMENDMENTS TO THE CLAIMS**

Please cancel Claims 53-59, 65, 67-69, 71 and 77.

1-71. (Cancelled).

72. (Previously Presented) A processing reactor for high temperature treatment of substrates, the reactor comprising:

a plurality of walls defining a chemical vapor deposition chamber;

a movable substrate support structure;

a heat source for heating a substrate upon the support structure within the chamber;

a thermal exchange member, wherein the thermal exchange member comprises a wall substantially transparent to radiant heat; and

a drive mechanism capable of moving the support structure between a substrate treatment position and a heat exchange position,

wherein the support structure supports the substrate during substrate treatment within the chamber at the substrate treatment position, and wherein the support structure also supports the substrate at the thermal exchange position while the substrate is spaced from the thermal exchange member by between about 0.2 mm and 3.0 mm to enable conductive heat transport between the thermal exchange member and the substrate.

73. (Previously Presented) The processing reactor of Claim 72, wherein the distance is between about 0.5 and 1.5 mm

74. (Previously Presented) The processing reactor of Claim 72, wherein the thermal exchange member is positioned within the chamber.

75. (Previously Presented) The processing reactor of Claim 74, wherein the thermal exchange member is one of the plurality of walls defining the chamber.

76. (Previously Presented) The processing reactor of Claim 72, wherein the thermal exchange member is actively cooled.

77. (Cancelled).